

Description

Advanced process capability has been used to maximise the performance of this 60V, NPN transistor. The W-DFN2020-3/SWP (Type A) package offers lower profile and the derating up to +175°C allows higher dissipation for applications where power density is of utmost importance.

Features

- $BV_{CEO} > 60V$
- $I_C = 4A$ Continuous Collector Current
- Low Saturation Voltage (100mV Max @1A)
- $R_{SAT} = 60m\Omega$ for a Low Equivalent On-Resistance
- h_{FE} Specified up to 6A for High Current Gain Hold Up
- Tighter Gain Specification
- Low Profile 0.62mm High Package for Thin Applications
- Sidewall Tin Plating for Wettable Flanks in AOI
- R_{0JA} Efficient, 60% Lower than SOT23
- 4mm² Footprint, 50% Smaller Than SOT23
- Rated +175°C – Ideal for High Temperature Environment
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DXTN10060DFJBWQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.**

Mechanical Data

- Case: W-DFN2020-3
- Nominal Package Height: 0.6mm
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin, Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.01 grams (Approximate)

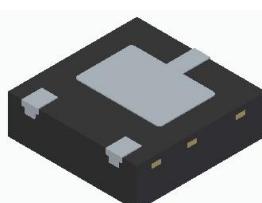
Applications

- Automotive Systems
 - MOSFET Gate Driving
 - DC-DC Converters
 - Motor Control
 - Power Switches

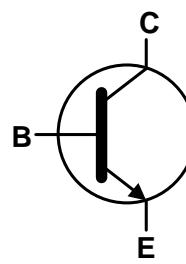
W-DFN2020-3/SWP (Type A)



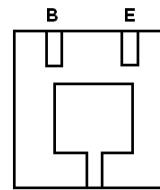
Top View



Bottom View



Device Symbol



Bottom View
Pin-Out

Ordering Information (Note 4)

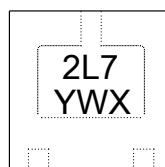
| Part Number | Compliance | Marking | Reel Size (inches) | Tape Width (mm) | Quantity Per Reel |
|-------------------|------------|---------|--------------------|-----------------|-------------------|
| DXTN10060DFJBWQ-7 | Automotive | 2L7 | 7 | 8 | 3,000 |

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

W-DFN2020-3/SWP (Type A)



2L7 = Product Type Marking Code

Y = Year: 0~9

W = Week: A~Z: 1~26 Week;

a~z; 27~52 Week; z Represents

52 and 53 Week

X = A~Z: Internal Code

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|------------------------------|-------------------------------|-------|------|
| Collector-Base Voltage | V_{CBO} | 100 | V |
| Collector-Emitter Voltage | V_{CEO} | 60 | |
| Emitter-Base Voltage | V_{EBO} | 8 | |
| Peak Pulse Current | I_{CM} | 6 | |
| Continuous Collector Current | I_C (Note 5) (Note 6) | 4 | A |
| | | 4.3 | |
| Base Current | I_B | 1 | |

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|---|-----------------------------|-------------|------------|
| Power Dissipation Linear Derating Factor | P_D (Note 5) | 1.8 | W mW/°C |
| | | 12 | |
| | $R_{\theta JA}$ (Note 6) | 2.94 | |
| | | 19.6 | |
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ (Note 5) | 83 | °C/W |
| | | 51 | |
| Thermal Resistance, Junction to Lead | $R_{\theta JL}$ (Note 7) | 16.8 | |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +175 | °C |

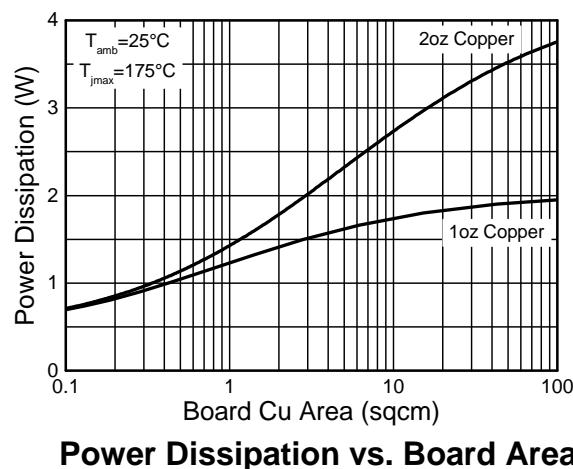
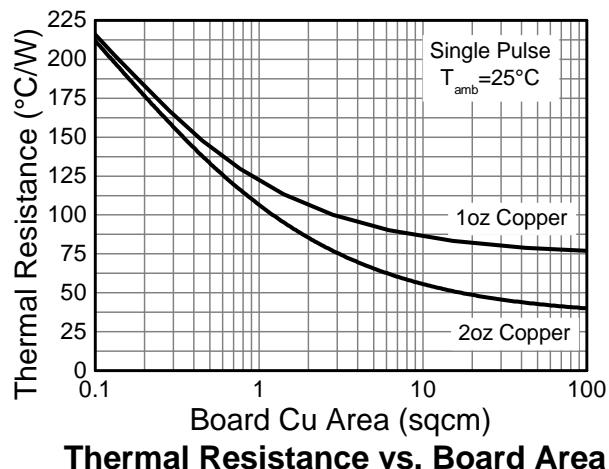
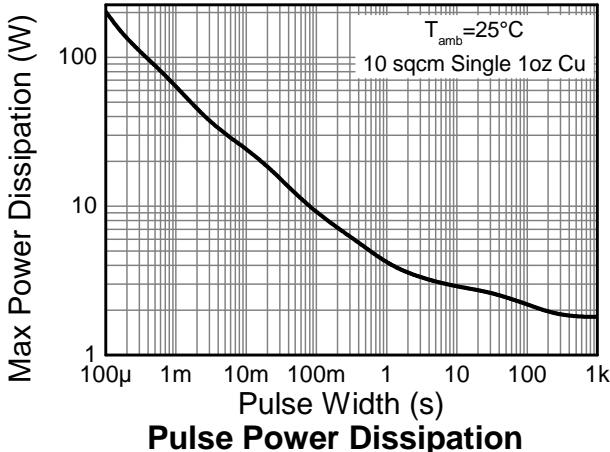
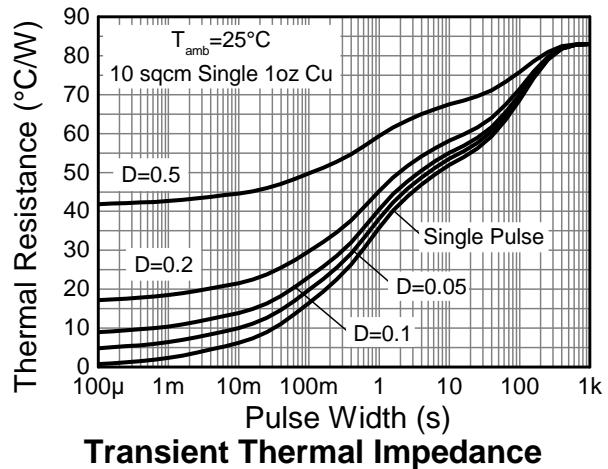
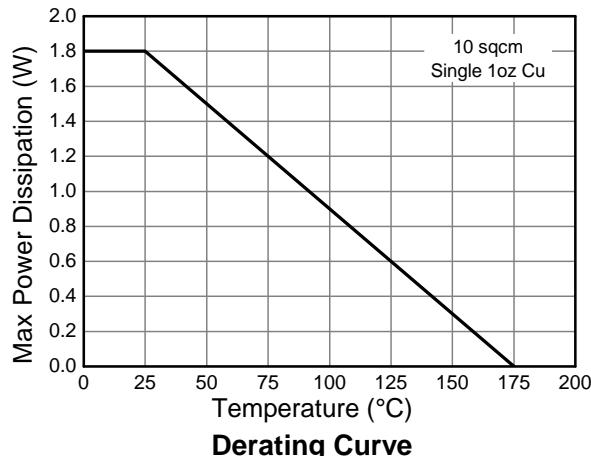
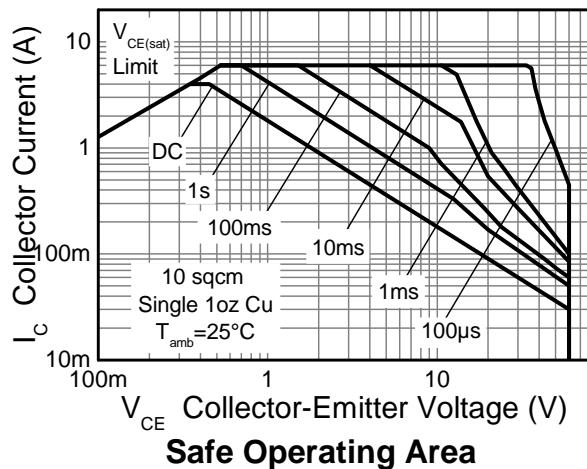
ESD Ratings (Note 8)

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V | 3A |
| Electrostatic Discharge - Machine Model | ESD MM | 400 | V | C |

Notes:

5. For a device mounted with the exposed collector pad on 31mm x 31mm (10cm²) 1oz copper that is on a single sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state. The entire exposed collector pad is attached to the heatsink.
6. Same as Note 5, except the device is measured at $t \leq 5$ sec.
7. Thermal resistance from junction to solder-point (on the exposed collector pad).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

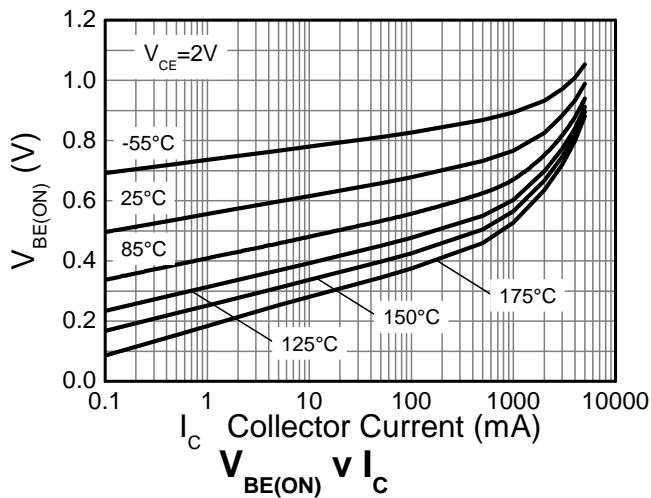
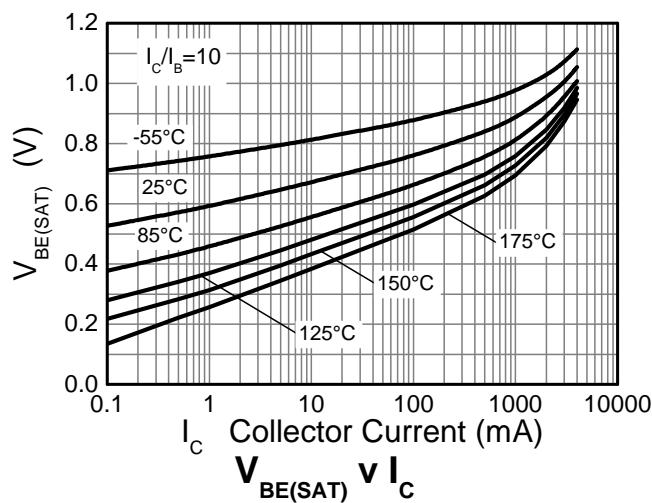
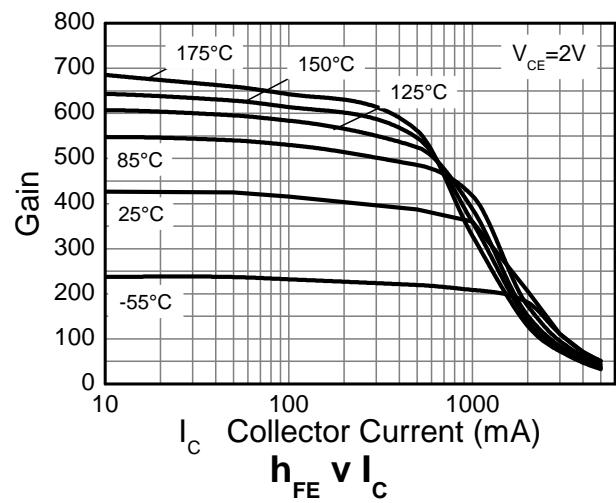
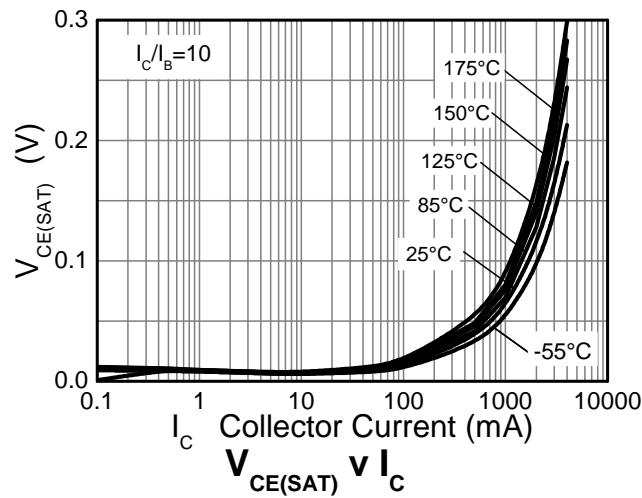
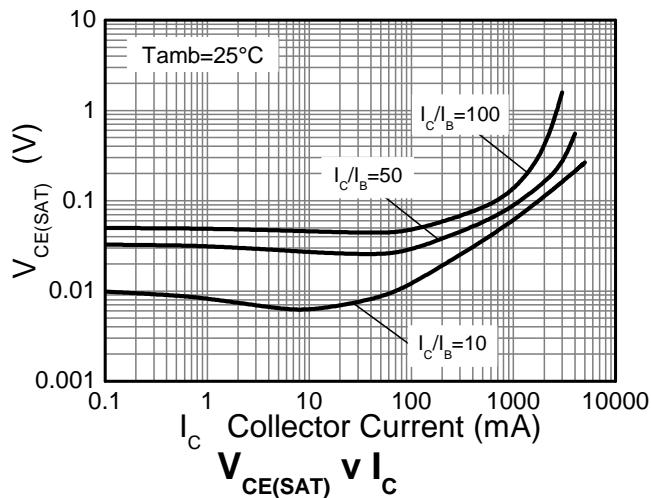


Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|-----------------------------|-----|------|------|------|--|
| Collector-Base Breakdown Voltage | BV_{CBO} | 150 | 187 | - | V | $I_C = 100\mu\text{A}$ |
| Collector-Emitter Breakdown Voltage (Note 9) | BV_{CEO} | 60 | 66 | - | V | $I_C = 10\text{mA}$ |
| Emitter-Base Breakdown Voltage | BV_{EBO} | 8 | 9 | - | V | $I_E = 100\mu\text{A}$ |
| Collector Cutoff Current | I_{CBO} | - | 2 | 100 | nA | $V_{\text{CB}} = 120\text{V}$ |
| Emitter Cutoff Current | I_{EBO} | - | 2 | 100 | nA | $V_{\text{EB}} = 7\text{V}$ |
| Collector Emitter Cutoff Current | I_{CES} | - | 2 | 100 | nA | $V_{\text{CES}} = 48\text{V}$ |
| Static Forward Current Transfer Ratio (Note 9) | h_{FE} | 250 | 444 | 550 | - | $I_C = 10\text{mA}, V_{\text{CE}} = 2\text{V}$ |
| | | 340 | 425 | 500 | | $I_C = 200\text{mA}, V_{\text{CE}} = 2\text{V}$ |
| | | 250 | 363 | -- | | $I_C = 1\text{A}, V_{\text{CE}} = 2\text{V}$ |
| | | 140 | 205 | -- | | $I_C = 2\text{A}, V_{\text{CE}} = 2\text{V}$ |
| | | 20 | 40 | -- | | $I_C = 6\text{A}, V_{\text{CE}} = 2\text{V}$ |
| | | -- | 12 | 20 | | $I_C = 0.1\text{A}, I_B = 10\text{mA}$ |
| Collector-Emitter Saturation Voltage (Note 9) | $V_{\text{CE}(\text{SAT})}$ | -- | 70 | 100 | mV | $I_C = 1\text{A}, I_B = 50\text{mA}$ |
| | | -- | 125 | 160 | | $I_C = 1\text{A}, I_B = 10\text{mA}$ |
| | | -- | 150 | 200 | | $I_C = 2\text{A}, I_B = 50\text{mA}$ |
| | | -- | 200 | 300 | | $I_C = 3\text{A}, I_B = 100\text{mA}$ |
| | | -- | 240 | 320 | | $I_C = 4\text{A}, I_B = 200\text{mA}$ |
| Base-Emitter Turn-On Voltage (Note 9) | $V_{\text{BE}(\text{ON})}$ | -- | 0.94 | 1.00 | V | $I_C = 4\text{A}, V_{\text{CE}} = 2\text{V}$ |
| Base-Emitter Saturation Voltage (Note 9) | $V_{\text{BE}(\text{SAT})}$ | -- | 1.00 | 1.07 | V | $I_C = 4\text{A}, I_B = 200\text{mA}$ |
| Output Capacitance | C_{obo} | -- | 14 | -- | pF | $V_{\text{CB}} = 10\text{V}, f = 1\text{MHz}$ |
| Transition Frequency | f_T | 125 | -- | -- | MHz | $V_{\text{CE}} = 10\text{V}, I_C = 50\text{mA}, f = 100\text{MHz}$ |
| Turn-On Time | t_{ON} | -- | 200 | -- | ns | $V_{\text{CC}} = 10\text{V}, I_C = 1\text{A}$ |
| Turn-Off Time | t_{OFF} | -- | 700 | -- | ns | $I_{B1} = -I_{B2} = 10\text{mA}$ |

Note: 9. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

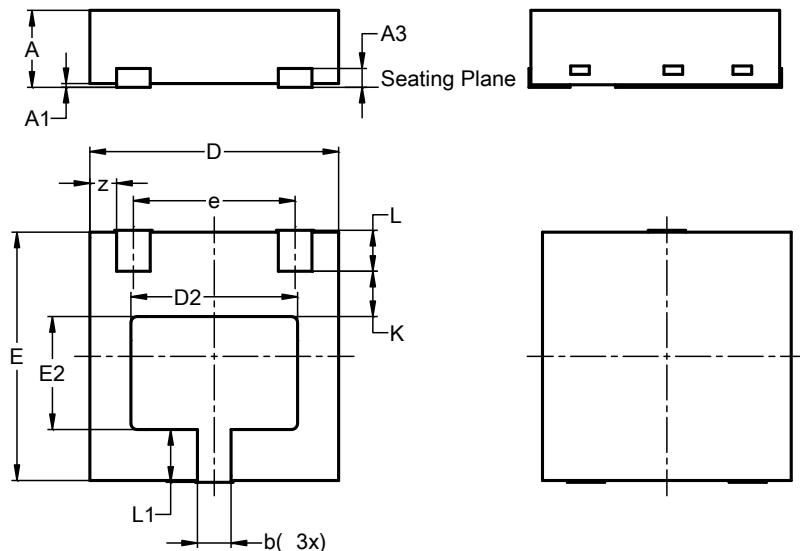
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

W-DFN2020-3/SWP (Type A)



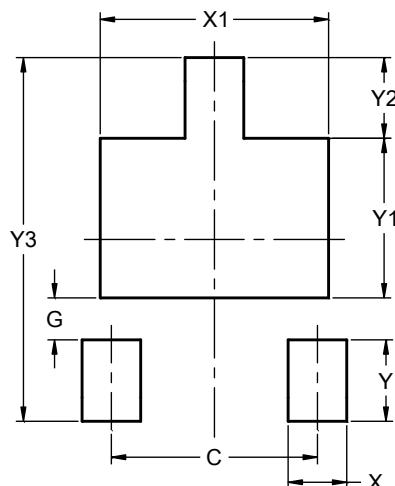
| W-DFN2020-3 /SWP (Type A) | | | |
|------------------------------|-------|-------|-------|
| Dim | Min | Max | Typ |
| A | 0.57 | 0.67 | 0.62 |
| A1 | 0.00 | 0.05 | 0.03 |
| A3 | — | — | 0.152 |
| b | 0.22 | 0.32 | 0.27 |
| D | 1.95 | 2.05 | 2.00 |
| D2 | 1.24 | 1.44 | 1.34 |
| D4 | 0.56 | 0.76 | 0.66 |
| E | 1.95 | 2.05 | 2.00 |
| E2 | 0.81 | 1.01 | 0.91 |
| e | — | — | 1.30 |
| K | — | — | 0.365 |
| L | 0.28 | 0.38 | 0.33 |
| L1 | 0.375 | 0.475 | 0.425 |
| z | — | — | 0.215 |

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

W-DFN2020-3/SWP (Type A)



| Dimensions | Value (in mm) |
|------------|------------------|
| C | 1.300 |
| G | 0.265 |
| X | 0.370 |
| X1 | 1.440 |
| Y | 0.515 |
| Y1 | 1.010 |
| Y2 | 0.510 |
| Y3 | 2.300 |

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